

SOLAR

InOxSide® EB

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Integrated PSG removal, junction isolation and emitter etch back

The InOxSide® EB ensures efficient junction isolation and PSG removal for high throughput solar cell production. With the integrated emitter etch back step, the InOxSide® EB offers an extra boost in blue response and improves cell efficiency as well as process reliability.

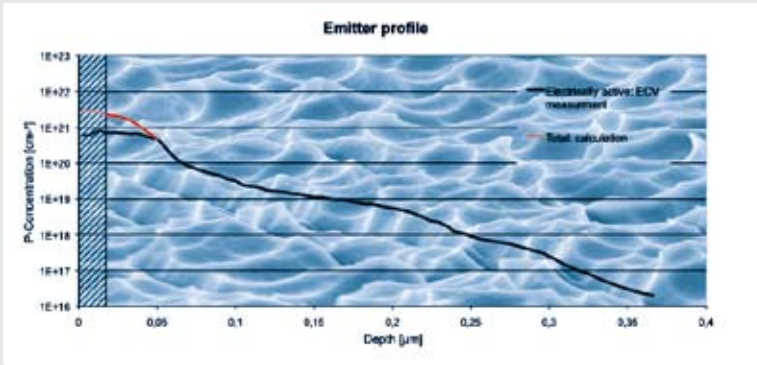
Areas of application

- PSG removal, junction isolation and emitter etch back
- Designed for multi- and monocrystalline wafers, Inline and POCl_3 -diffusion
- Wafer transfer systems available for automatic loading and unloading

Features and benefits

- PSG removal, junction isolation and emitter etch back in one single tool
 - Straight line and optimised footprint
 - Ideal process and work flow integration
- Technological leadership
 - Process start up by RENA
 - Minimum total cost of ownership
 - Stable and reproducible processing





Front view InOxSide® EB

Technical Data InOxSide® EB

InOxSide® EB HT	
Platform	NIAK 5 lanes for 156 mm wafers
Process	Inline PSG removal, junction isolation and emitter etch back
Dimensions	10800 x 2150 x 2350 mm (length x width x height)
Throughput	3600 wafers/h gross *) wafer size 156 mm
Wafer thickness	> 150 µm

*) Tool with reduced throughput available upon request.